

**In the Specification:**

Page 1, line 1, please cancel the existing title "CMOS Structure and Related Method" and substitute --Method and Structure for CMOS Devices with Stress Relaxed by Ion Implantation of Carbon or Oxygen Containing Ions--.

Page 16, line 1, please cancel the existing title "CMOS Structure and Related Method" and substitute -- Method and Structure for CMOS Devices with Stress Relaxed by Ion Implantation of Carbon or Oxygen Containing Ions--.